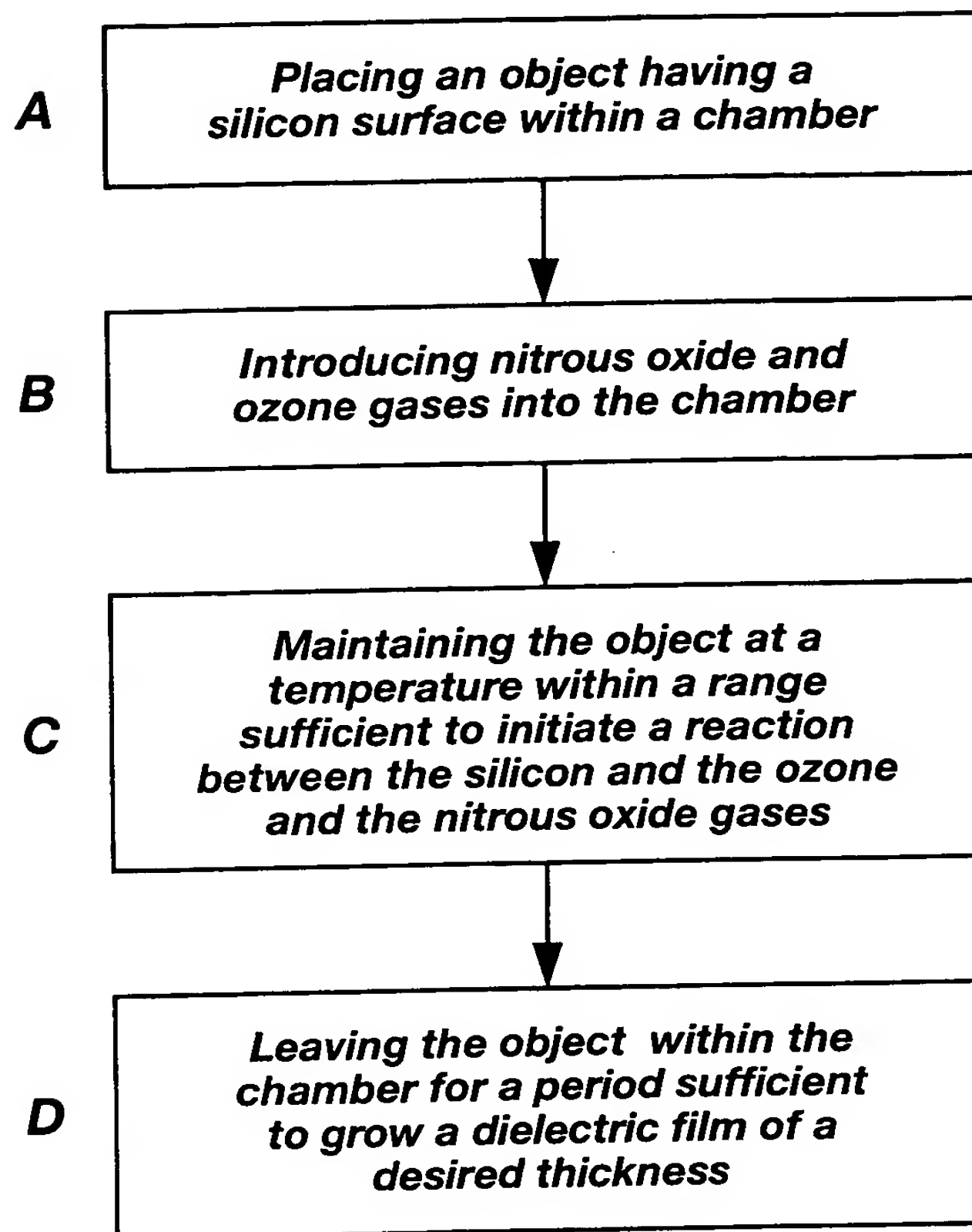


TITLE: PROCESS FOR GROWING A DIELECTRIC LAYER ON A  
SILICON-CONTAINING SURFACE USING A MIXTURE OF N<sub>2</sub>O  
AND O<sub>3</sub>

Inventor: Sandhu et al.  
Docket No.: 3980.3US

1/1



**FIG. 1**